

High voltage fast-switching NPN power transistor

Features

- Integrated antiparallel collector-emitter diode
- High voltage capability
- Minimum lot-to-lot spread for reliable operation
- Very high switching speed

Applications

- Electronic ballast for fluorescent lighting
- Flyback and forward single transistor low power converters



The device is manufactured using high voltage multi-epitaxial planar technology for high switching speeds and medium voltage capability.

It uses a cellular emitter structure with planar edge termination to enhance switching speeds while maintaining the wide RBSOA.

The device is designed for use in lighting applications and low cost switch-mode power supplies.

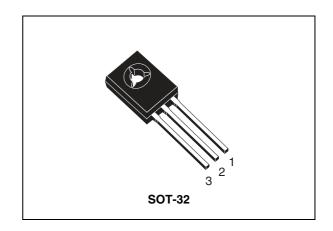


Figure 1. Internal schematic diagram

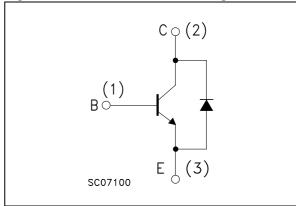


Table 1. Device summary

Order codes	Marking	Package	Packaging
STT13005D	T13005D	SOT-32	Tube
STT13005D-K	T13005D	SOT-32	Bag

Electrical ratings STT13005D

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CES}	Collector-emitter voltage (V _{BE} = 0)	700	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	400	V
V _{EBO}	Emitter-base voltage (I _C = 0)	9	٧
I _C	Collector current	2	Α
I _{CM}	Collector peak current (t _P < 5 ms)	4	Α
I _B	Base current	1	Α
I _{BM}	Base peak current (t _P < 5 ms)	2	Α
P _{TOT}	Total dissipation at T _c = 25 °C	45	W
T _{STG}	Storage temperature	-65 to 150	°C
T _J	Max. operating junction temperature	150	°C

Table 3. Thermal data

Symbo	Parameter Parameter	Value	Unit
R _{thJC}	Thermal resistance junction-case Max	2.8	°C/W

2 Electrical characteristics

 T_{case} = 25 °C unless otherwise specified.

Table 4. Electrical characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector cut-off current (V _{BE} = 0)	V _{CE} = 700 V V _{CE} = 700 V T _C = 125 °C			100 500	μ Α μ Α
I _{CEO}	Collector cut-off current (I _B = 0)	V _{CE} = 400 V			250	μΑ
V _{EBO}	Emitter-base voltage $(I_C = 0)$	I _E = 10 mA	9			V
V _{CEO(sus)} (1)	Collector-emitter sustaining voltage (I _B = 0)	I _C = 10 mA	400			V
V _{CE(sat)} (1)	Collector-emitter saturation voltage	$\begin{split} I_{C} &= 0.5 \text{ A} & I_{B} = 125 \text{ mA} \\ I_{C} &= 0.8 \text{ A} & I_{B} = 0.2 \text{ A} \\ I_{C} &= 1.6 \text{ A} & I_{B} = 0.4 \text{ A} \end{split}$			0.5 1 1.5	>
V _{BE(sat)} (1)	Base-emitter saturation voltage	$\begin{split} I_C &= 0.5 \text{ A} & I_B = 125 \text{ mA} \\ I_C &= 0.8 \text{ A} & I_B = 0.2 \text{ A} \\ I_C &= 1.6 \text{ A} & I_B = 0.4 \text{ A} \end{split}$			1 1.3 1.5	< < <
h _{FE} ⁽¹⁾	DC current gain	$I_C = 0.5 \text{ A}$ $V_{CE} = 5 \text{ V}$ $I_C = 2 \text{ A}$ $V_{CE} = 5 \text{ V}$	10 8		50	
t _r t _s	Resistive load Rise time Storage time Fall time	$I_C = 1 A$ $V_{CC} = 125 V$ $I_{B1} = -I_{B2} = 0.2 A$		0.4 3.2 0.25	0.7 4.5 0.4	he he
t _s	Inductive load Storage time Fall time	$\begin{split} I_{C} &= 1 \text{ A} & I_{B1} = 0.2 \text{ A} \\ V_{BE(off)} &= -5 \text{ V} & L = 50 \text{ mH} \\ V_{Clamp} &= 300 \text{ V} \end{split}$		0.8 0.16		μs μs
V_{F}	Diode forward voltage	I _F = 1 A			2.5	V

^{1.} Pulse test: pulse duration $\leq 300~\mu s,$ duty cycle $\leq 2~\%$

Electrical characteristics STT13005D

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

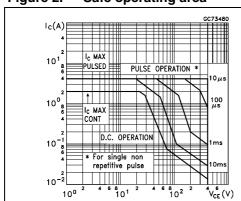


Figure 3. Derating curve

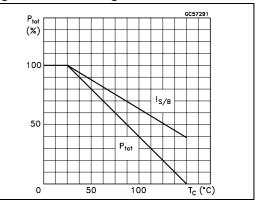
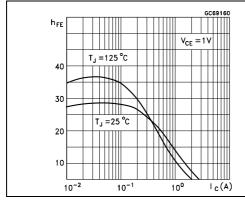


Figure 4. DC current gain $(V_{CE} = 1 V)$ I

Figure 5. DC current gain $(V_{CE} = 5 V)$



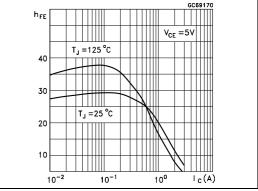
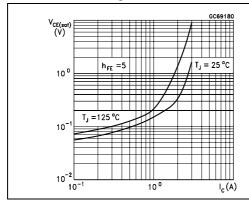


Figure 6. Collector-emitter saturation voltage

Figure 7. Base-emitter saturation voltage



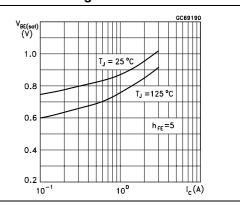


Figure 8. Inductive load fall time

t_f(ns)

V_{Clamp} = 300 V

h_{FE} = 5

R_{BB} = 0Ω

V_{BE}(off) = -5V

T_J = 125 °C

T_J = 25 °C

300

0 0.5 1 1.5 2 I_C(A)

Figure 9. Inductive load storage tim

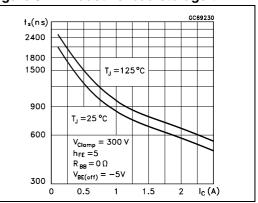


Figure 10. Resistive load fall time

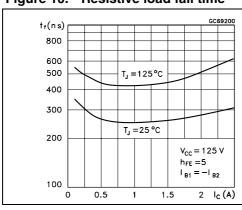


Figure 11. Resistive load storage time

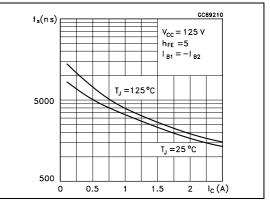
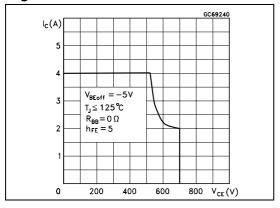


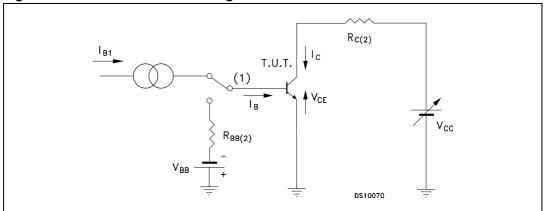
Figure 12. Reverse biased SOA



Electrical characteristics STT13005D

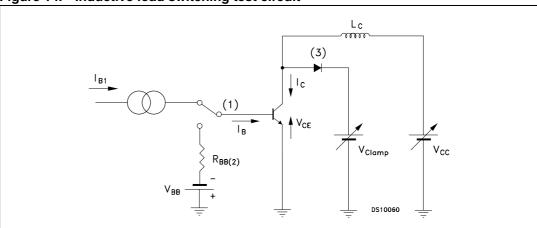
2.2 Test circuits

Figure 13. Resistive load switching test circuit



- 1. Fast electronic switch
- 2. Non-inductive resistor

Figure 14. Inductive load switching test circuit

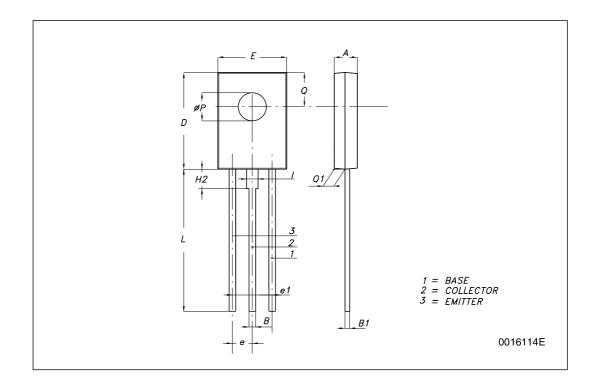


- 1. Fast electronic switch
- 2. Non-inductive resistor
- 3. Fast recovery rectifier

3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

DIM.	mm.		
	MIN.	ТҮР	MAX.
Α	2.4		2.9
В	0.64		0.88
B1	0.39		0.63
D	10.5		11.05
Е	7.4		7.8
е	2.04	2.29	2.54
e1	4.07	4.58	5.08
L	15.3		16
Р	2.9		3.2
Q		3.8	
Q1	1		1.52
H2		2.15	
1		1.27	



STT13005D Revision history

4 Revision history

Table 5. Document revision history

Date	Revision	Changes
10-Jul-2008	1	Initial release.
03-Nov-2009	2	Added order code STT13005D-K Table 1 on page 1.

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2009 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

10/10 Doc ID 14897 Rev 2

